

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	173683	FET or (field near effect near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:28
L2	5645	(contact near hole\$1) same (salicide or silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:34
L3	193690	(silicon near nitride) or SiN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:35
L4	307601	(silicon near oxide) or (silicon near dioxide) or "SiO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:38
L5	46113	interlayer\$2 near (dielectric or insulat\$3 or isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:39
L6	12204	I3 and I4 and I5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:39
L7	1104	I2 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:40
L8	34975	((etch\$3 near rate) or (etching near selection near ratio))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:42
L9	382	I7 and I8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/12 09:42